

# MM54C910/MM74C910 256 Bit TRI-STATE® Random Access Read/Write Memory

## **General Description**

The MM54C910/MM74C910 is a 64 word by 4-bit random access memory. Inputs consist of six address lines, four data input lines, a WE, and a  $\overline{\text{ME}}$  line. The six address lines are internally decoded to select one of the 64 word locations. An internal address register latches the address information on the positive to negative transition of  $\overline{\text{ME}}$ . The TRI-STATE outputs allow for easy memory expansion.

Address Operation: Address inputs must be stable ( $t_{SA}$ ) prior to the positive to negative transition of  $\overline{ME}$ , and ( $t_{HA}$ ) after the positive to negative transition of  $\overline{ME}$ . The address register holds the information and stable address inputs are not needed at any other time.

Write Operation: Data is written into memory at the selected address if  $\overline{WE}$  goes low while  $\overline{ME}$  is low.  $\overline{WE}$  must be held low for  $t_{\overline{WE}}$  and data must remain stable  $t_{HD}$  after  $\overline{WE}$  returns high.

Read Operation: Data is nondestructively read from a memory location by an address operation with  $\overline{\text{WE}}$  held high.

ADDRESS

Outputs are in the TRI-STATE (Hi-Z) condition when the device is writing or disabled.

### Features

CIRCUITRY

ABBAY

READ/WR

Supply voltage range
Supply voltage range
With a second structure
High noise immunity
Mathematical Structure
TTL compatible fan out
TTL compatible fan out
TTL compatible fan out
TTL load
Input address register
Low power consumption
250 nW/package (typ.) (chip enabled or disabled)
Fast access time
250 ns (typ.) at 5.0V
TRI-STATE outputs
High voltage inputs



TRI-STATE = ME + WE

WRITE O

ADDRESS INPUTS



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	te Maximum Ra	tings (	Note 1)	0	pera	ating Con	ditions Min	Max	Units
If Military/Aerospace specified devices an please contact the National Semicondu			ctor Sales Supply Volta finations MM54C91		ly Voltage (V <sub>CC</sub> 454C910	;) 4.5	5.5	V	
Voltage at Apy Output Pip				MN	//74C910	4.75	5.25	v	
Voltage at Any Dulput Pin -0.3V to		$3V_{CC} + 0.3V$		Tem	perature (T <sub>A</sub> )				
Power Dissipation		.30 10 1 150		M	A54C910	-55	+ 125	°C °C	
Dual-In-Line			700 mW		IVII	1740910	-40	+ 65	U
Small Outl	ine		500 mW						
Operating V <sub>CC</sub> Range		:	3.0V to 5.5V						
Standby V <sub>CC</sub> Range			1.5V 10 5.5V 6 0V						
Lead Tempe (Soldering	erature (T <sub>L</sub> ) , 10 sec.)		260°C						
	trical Characte	ristics	and power si	upply rang	e indic	ated			
Symbol	Parameter		Condit	tions		Min	Тур	Мах	Unit
V <sub>IN(1)</sub>	Logical "1" Input Vol	tage	Full Ran	ge	Vc	<sub>CC</sub> – 1.5			V
V <sub>IN(0)</sub>	Logical "0" Input Vol	tage	Full Ran	ge				0.8	V
I <sub>IN(1)</sub>	Logical "1" Input Cur	rent	V <sub>IN</sub> = 15	5V			0.005	2.0	μΑ
			$V_{IN} = 5$	V			0.005	1.0	μΑ
I <sub>IN(0)</sub>	Logical "0" Input Cur	rent	$V_{IN} = 0$	V		-1.0	-0.005		μΑ
V <sub>OUT(1)</sub>	Logical "1" Output Ve	oltage	$l_0 = -1$ $l_0 = -2$	150 μA 100 μA	Vc	<sub>CC</sub> - 0.5 2.4			v v
V <sub>OUT(0)</sub>	Logical "0" Output Ve	oltage	l <sub>O</sub> = 1.6	mA				0.4	V
I <sub>OZ</sub>	Output Current in Hig Impedance State	h	$V_{O} = 5V_{O} = 0V_{O}$	5V 0V -1.0		-1.0	0.005 	1.0	μA μA
I <sub>CC</sub> Supply Current			$V_{CC} = 5V$				5.0	300	μA
AC Elec	trical Characte	ristics	<b>*</b> T <sub>A</sub> = 25°	°C, V <sub>CC</sub> =	5.0V, (	C <sub>L</sub> = 50 pF			
Symbol Parameter		ameter		Min		Тур	Max		Units
t <sub>ACC</sub>	Access Time	from Addr	ess			250	500		ns
t <sub>pd</sub>	Propagation I	Delay from	ME			180	360		ns
t <sub>SA</sub>	Address Inpu	t Set-Up T	Jp Time			70			ns
t <sub>HA</sub> Address Input Hold		t Hold Tim	ne 20			10			ns
twee Memory Enable Pulse		ole Pulse V	Width 200			100			ns
tME Memory Enable Pulse		ole Pulse V	Width 400			200			ns
t <sub>SD</sub> Data Input Set-Up Time		et-Up Time	e 0						ns
t <sub>HD</sub> Data Input Hold Time		30			15			ns	
tWE Write Enable Pulse Wit		dth 140			70			ns	
t <sub>1H</sub> , t <sub>0H</sub> Delay to TRI-STATE (N		ote 4)			100	200		ns	
PACITANCI	E							·	
C <sub>IN</sub> Input Capacity Any Input (Note 2)		y ote 2)				5.0			pF
C <sub>OUT</sub> Output Capacity		city Note 2)				9.0			pF
C <sub>PD</sub> Power Dissipation Cap		acity			050			nE	

Symbol	Parameter	MM5 T <sub>A</sub> = -55° V <sub>CC</sub> = 4.	4C910 C to  + 125°C 5V to 5.5V	$\begin{array}{l} \mbox{MM74C910} \\ \mbox{T}_{\mbox{A}} = -40^{\circ}\mbox{C to} +85^{\circ}\mbox{C} \\ \mbox{V}_{\mbox{CC}} = 4.75\mbox{V to} 5.25\mbox{V} \end{array}$		Units
		Min	Max	Min	Max	
t <sub>ACC</sub>	Access Time from Address		860		700	ns
t <sub>pd1</sub> , t <sub>pd0</sub>	Propagation Delay from $\overline{\text{ME}}$		660		540	ns
t <sub>SA</sub>	Address Input Set-Up Time	200		160		ns
t <sub>HA</sub>	Address Input Hold Time	20		20		ns
t <sub>ME</sub>	Memory Enable Pulse Width	280		260		ns
tME	Memory Enable Pulse Width	750		600		ns
t <sub>SD</sub>	Data Input Set-Up Time	0		0		ns
t <sub>HD</sub>	Data Input Hold Time	50		50		ns
tWE	Write Enable Pulse Width	200		180		ns
t <sub>1H</sub> , t <sub>0H</sub>	Delay to TRI-STATE (Note 4)		200		200	ns

\*AC Parameters are guaranteed by DC correlated testing.

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Capacitance is guaranteed by periodic testing.

Note 3: CPD determines the no load AC power consumption for any CMOS device. For complete explanation see 54C/74C Family Characteristics application note AN-90.

Note 4: See AC test circuits for  $t_{1H}$ ,  $t_{0H}$ .

## **Typical Performance Characteristics**



Truth Table						
ME WE		Operation	Outputs			
L	L	Write	TRI-STATI			

		operation	Calpalo
L	L	Write	TRI-STATE
L	н	Read	Data
н	L	Inhibit, Store	TRI-STATE
н	н	Inhibit, Store	TRI-STATE

# **AC Test Circuits**













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